# Hex Schmitt-Trigger Inverter with LSTTL Compatible Inputs

## **High-Performance Silicon-Gate CMOS**

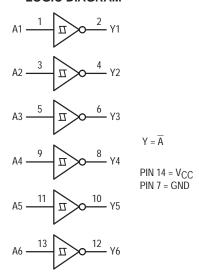
The MC74HCT14A may be used as a level converter for interfacing TTL or NMOS outputs to high–speed CMOS inputs.

The HCT14A is identical in pinout to the LS14.

The HCT14A is useful to "square up" slow input rise and fall times. Due to the hysteresis voltage of the Schmitt trigger, the HCT14A finds applications in noisy environments.

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS–Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates

#### LOGIC DIAGRAM



#### **FUNCTION TABLE**

Input A	Output Y
L	Н
Н	L

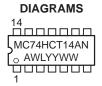


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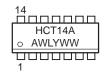
PDIP-14 N SUFFIX CASE 646



**MARKING** 



SOIC-14 D SUFFIX CASE 751A



= Assembly Location

WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

#### **PIN ASSIGNMENT**

A1 [	1•		v <sub>cc</sub>
Y1 [	2	13	] A6
A2 [	3		□ Y6
Y2 [	4	11	<b>A</b> 5
А3 [	5	10	Y5
Y3 [	6	9	] A4
ND [	7	8	1 Y4

G

#### **ORDERING INFORMATION**

Device	Package	Shipping
MC74HCT14AN	PDIP-14	2000 / Box
MC74HCT14AD	SOIC-14	55 / Rail
MC74HCT14ADR2	SOIC-14	2500 / Reel

#### **MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
l <sub>in</sub>	DC Input Current, per Pin	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin	± 25	mA
ICC	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C °C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$  VCC. Unused inputs must always be

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

Functional operation should be restricted to the Recommended Operating Conditions

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
Vcc	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	VCC	V
TA	Operating Temperature, All Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	_	*	ns

<sup>\*</sup>No Limit when  $V_{in} \approx$  50%  $V_{CC}$ ,  $I_{CC}$  > 1 mA.

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Temperature Limit						
			Vcc	– 55 to 25°C		≤ 85°C		≤ 125°C		
Symbol	Parameter	Test Conditions	Volts	Min	Max	Min	Max	Min	Max	Unit
V <sub>T+</sub> max	Maximum Positive–Going Input Threshold Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 5.5		1.9 2.1		1.9 2.1		1.9 2.1	V
V <sub>T+</sub> min	Minimum Positive–Going Input Threshold Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 5.5	1.2 1.4		1.2 1.4		1.2 1.4		V
V <sub>T</sub> _ max	Maximum Positive–Going Input Threshold Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 5.5		1.2 1.4		1.2 1.4		1.2 1.4	
V <sub>T</sub> _ min	Minimum Positive–Going Input Threshold Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 5.5	0.5 0.6		0.5 0.6		0.5 0.6		
V <sub>H</sub> max	Maximum Hysteresis Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 5.5		1.4 1.5		1.4 1.5		1.4 1.5	
V <sub>H</sub> min	Minimum Hysteresis Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 5.5	0.4 0.4		0.4 0.4		0.4 0 4		
VOH	Minimum High–Level Output Voltage	$V_{in} < VT$ -min $ I_{out}  \le 20 \mu A$	4.5 5.5	4.4 5.4		4.4 5.4		4.4 5.4		V
		$V_{in} < VT$ -min $ I_{Out}  \le 4.0 \text{ mA}$	4.5	3.98		3.84		3.7		

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High—Speed CMOS Data Book (DL129/D). (continued)

<sup>\*</sup>Maximum Ratings are those values beyond which damage to the device may occur.

<sup>†</sup>Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

#### DC CHARACTERISTICS (Voltages Referenced to GND) - continued

			Temperature Limit							
			VCC	– 55 to 25°C		≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Test Conditions	Volts	Min	Max	Min	Max	Min	Max	Unit
VOL	Maximum Low–Level Output Voltage	$V_{in} \ge VT + max$ $ I_{out}  \le 20 \mu A$	4.5 5.5		0.1 0.1		0.1 0.1		0.1 0.1	V
		$V_{in} \ge VT + max$ $ I_{out}  \le 4.0 \text{ mA}$	4.5		0.26		0.33		0.4	
lin	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5		± 0.1		± 1.0		±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0 μA	5.5		1.0		10		40	μА
					≥ - ₹	25°C to ≥-55°C 125°C				
ΔlCC	Additional Quiescent Supply Current	$V_{in}$ = 2.4 V, Any One Input $V_{in}$ = V <sub>CC</sub> or GND, Other Inputs $I_{out}$ = 0 $\mu$ A	5.5		2	.9	2	.4		mA

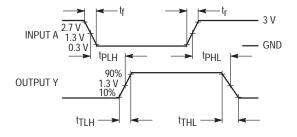
#### AC CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_f = t_f = 6.0 \text{ ns}$ )

				Guaranteed Limit  - 55 to 25°C ≤ 85°C		it				
								≤ 125°C		
Symbol	Parameter	Test Conditions		Min	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (L to H)	$V_{CC} = 5.0 \text{ V} \pm 10\%$ $C_L = 50 \text{ pF}, \text{ Input } t_f = t_f = 6.0 \text{ ns}$	Fig. 1 & 2		32		40		48	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time. Any Output	$V_{CC} = 5.0 \text{ V} \pm 10\%$ $C_L = 50 \text{ pF}, \text{ Input } t_f = t_f = 6.0 \text{ ns}$	Fig. 1 & 2		15		19		22	ns

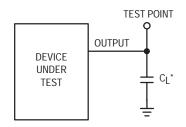
NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Per Inverter)*	32	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).





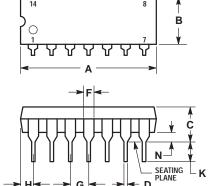


\*Includes all probe and jig capacitance

Figure 2. Test Circuit

#### **PACKAGE DIMENSIONS**

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE L

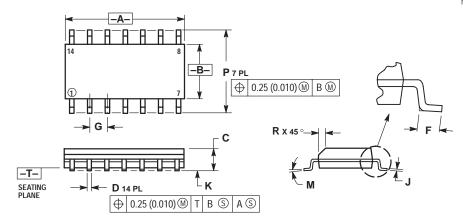




- NOTES:
  1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
  2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  4. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.715	0.770	18.16	19.56	
В	0.240	0.260	6.10	6.60	
С	0.145	0.185	3.69	4.69	
D	0.015	0.021	0.38	0.53	
F	0.040	0.070	1.02	1.78	
G	0.100 BSC		2.54	BSC	
Н	0.052	0.095	1.32	2.41	
J	0.008	0.015	0.20	0.38	
K	0.115	0.135	2.92	3.43	
L	0.300	BSC	7.62 BSC		
M	0°	10°	0°	10°	
N	0.015	0.039	0.39	1.01	

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE F



- OLES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE
  MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006)
   PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	S INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050	BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

## **Notes**

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JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

Phone: 81-3-5740-2745 Email: r14525@onsemi.com

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